

High Current MegaMOS™ FET

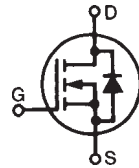
IXTK 250N10

$$V_{DSS} = 100 \text{ V}$$

$$I_{D25} = 250 \text{ A}$$

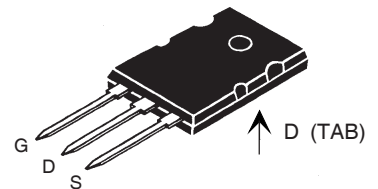
$$R_{DS(on)} = 5 \text{ m}\Omega$$

N-Channel Enhancement Mode



Symbol	Test conditions	Maximum ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1.0 \text{ M}\Omega$	100	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$ MOSFET chip capability	250	A
$I_{D(RMS)}$	External lead current limit	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	1000	A
I_{AR}	$T_C = 25^\circ\text{C}$	90	A
E_{AR}	$T_C = 25^\circ\text{C}$	80	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	4.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	730	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	0.7/6	Nm/lb.in.
Weight	TO-264	10	g

TO-264 AA (IXTK)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- International standard package
- Fast switching times

Applications

- Motor controls
- DC choppers
- Switched-mode power supplies
- DC-DC Converters
- Linear Regulators

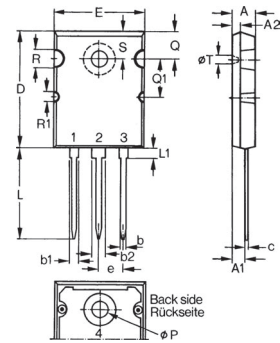
Advantages

- Easy to mount with one screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
(T _J = 25°C unless otherwise specified)				
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$			$50 \mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 90 \text{ A}$ Pulse test, $t \leq 300 \text{ ms}$, duty cycle $d \leq 2\%$			5 mΩ

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 90\text{ A}$, pulse test	75	110	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		12700	pF
C_{oss}			3700	pF
C_{rss}			1490	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 90\text{ A}$ $R_G = 1.0\ \Omega$ (External)		35	ns
t_r			40	ns
$t_{d(off)}$			120	ns
t_f			55	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		430	nC
Q_{gs}			70	nC
Q_{gd}			225	nC
R_{thJC}		0.15		0.17 K/W
R_{thCK}				K/W

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Source-Drain Diode

Ratings and Characteristics

($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Conditions	Ratings and Characteristics		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			250 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			1000 A
V_{SD}	$I_F = 90\text{ A}, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.2 V
t_{rr}	$I_F = 30\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 50\text{ V}$		150	ns
Q_{rr}			2	μC

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	6,404,065B1	6,162,665	6,534,343	6,583,505
4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1	6,259,123B1	6,306,728B1	6,683,344

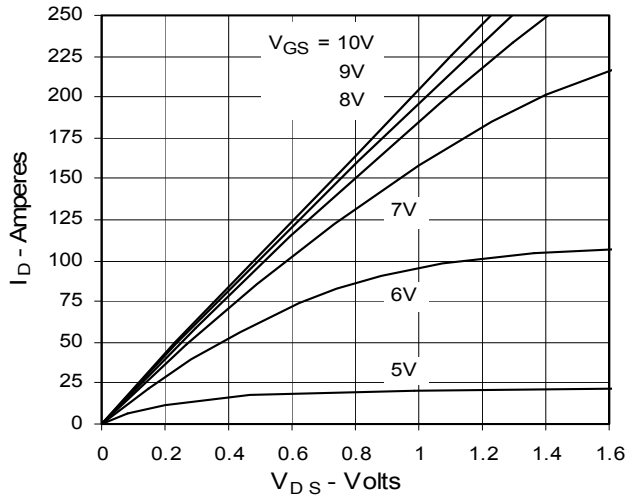
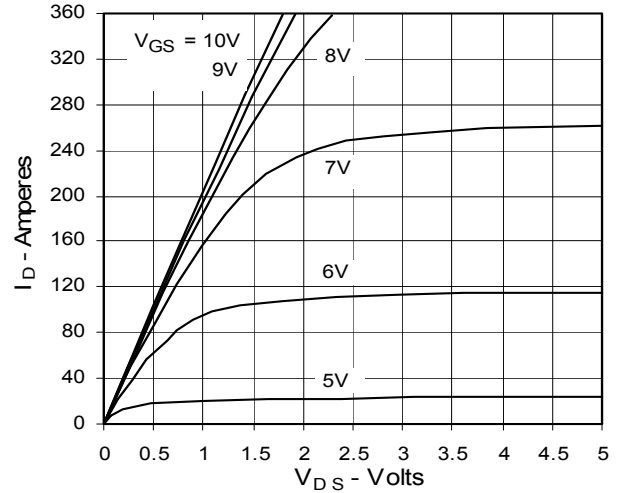
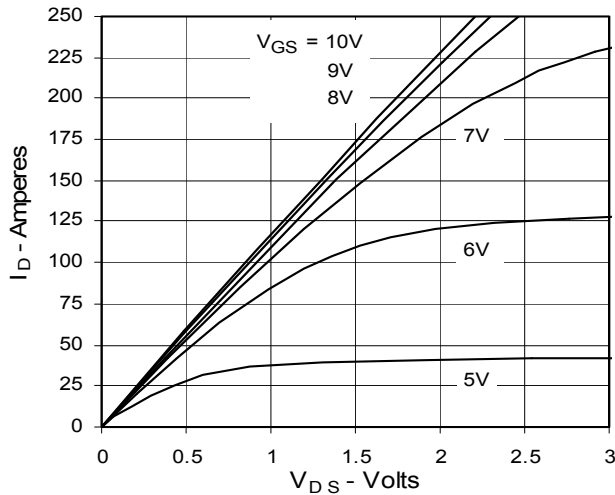
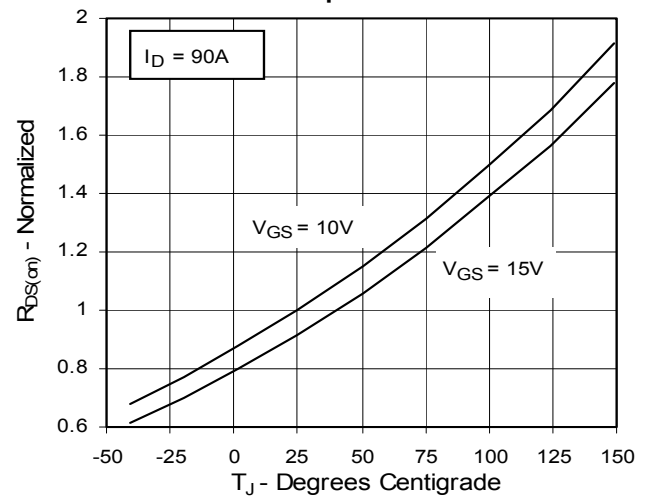
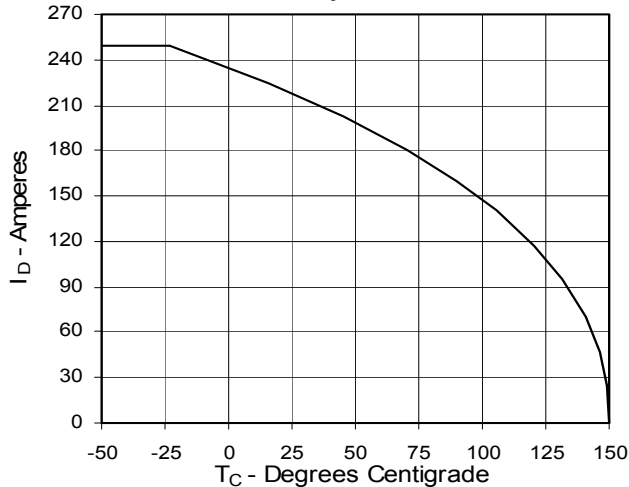
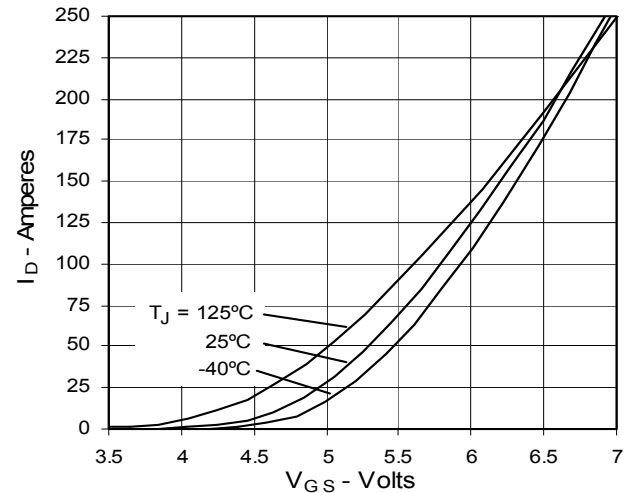
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

Fig. 4. Normalized $R_{DS(on)}$ vs. Junction Temperature

Fig. 5. Drain Current vs. Case Temperature

Fig. 6. Input Admittance


Fig. 7. Transconductance

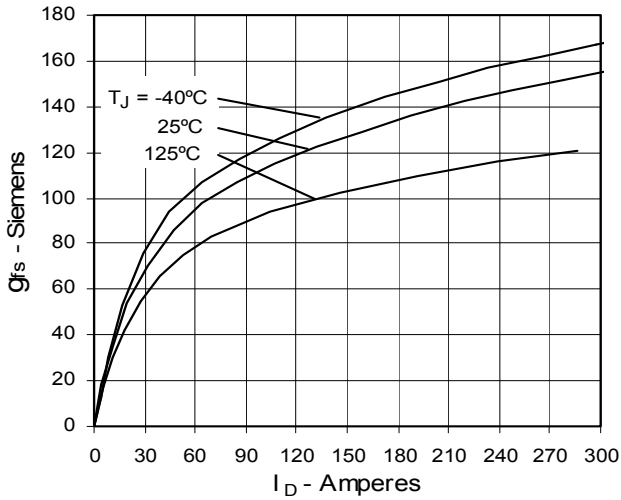


Fig. 8. Source Current vs. Source-To-Drain Voltage

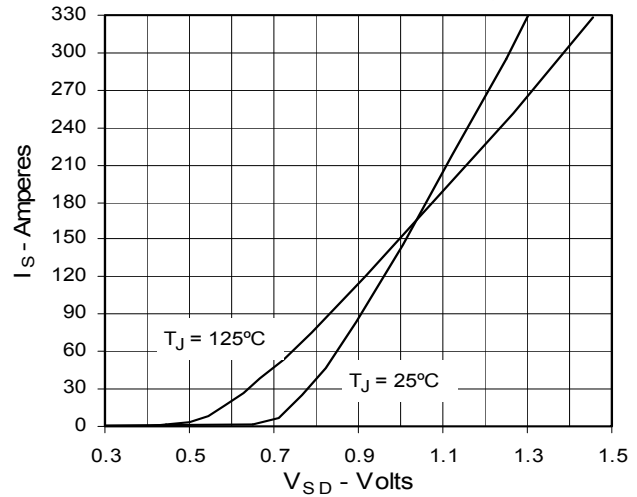


Fig. 9. Gate Charge

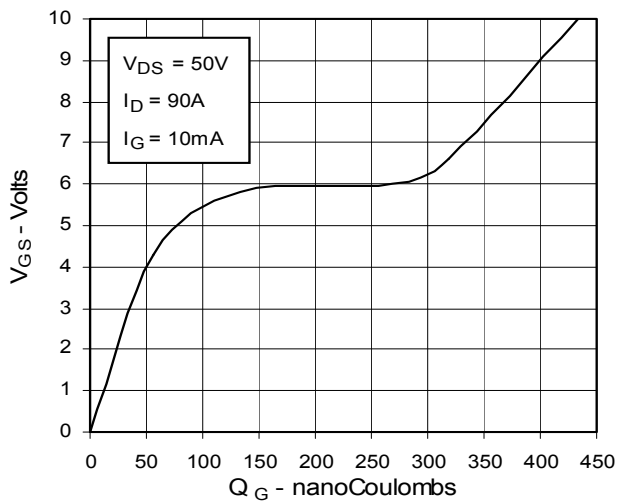


Fig. 10. Capacitance

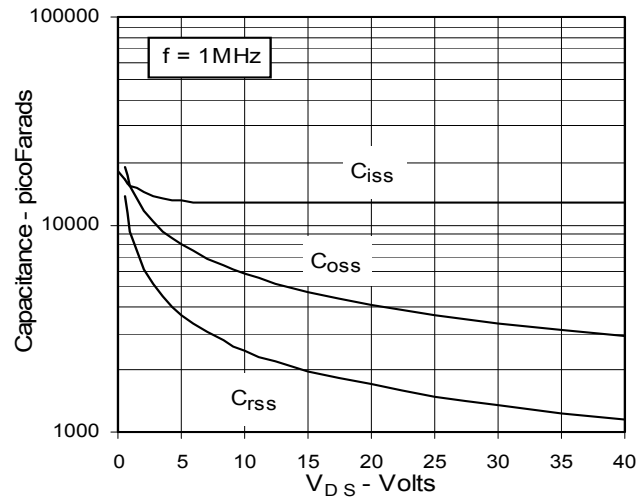


Fig. 11. Forward-Bias Safe Operating Area

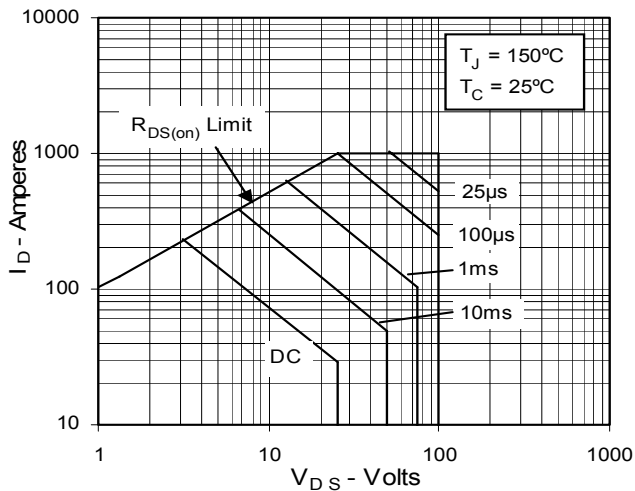
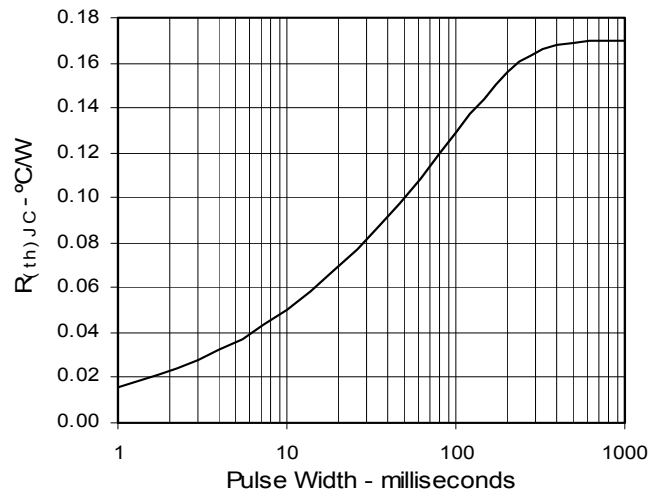


Fig. 12. Maximum Transient Thermal Resistance



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